



## DTA144T

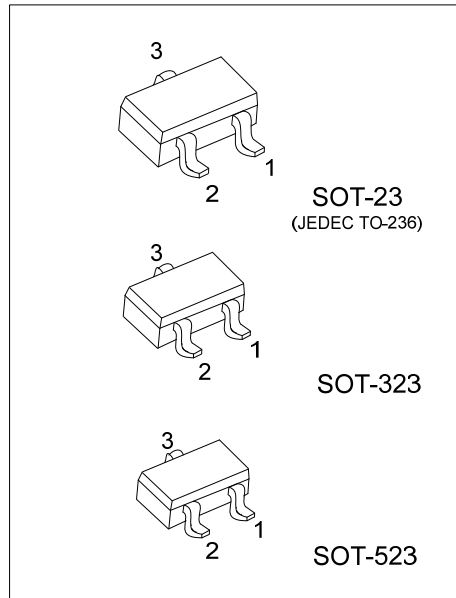
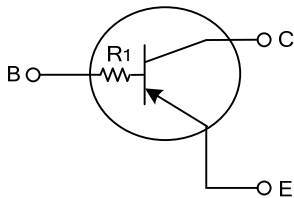
### PNP SILICON TRANSISITOR

## PNP DIGITAL TRANSISTOR (BUILT-IN RESISTOR)

### ■ FEATURES

- \* Built-in bias resistors that implies easy ON/OFF applications.
- \* The bias resistors are thin-film resistors with complete isolation to allow positive input.

### ■ EQUIVALENT CIRCUIT



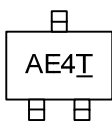
### ■ ORDERING INFORMATION

Ordering Number	Package	Pin Assignment			Packing
		1	2	3	
DTA144TG-AE3-R	SOT-23	E	B	C	Tape Reel
DTA144TG-AL3-R	SOT-323	E	B	C	Tape Reel
DTA144TG-AN3-R	SOT-523	E	B	C	Tape Reel

Note: Pin Assignment: B: Base C: Collector E: Emitter

<p>DTA144TG-AE3-R</p>	<p>(1) R: Tape Reel</p> <p>(2) AE3: SOT-23, AL3: SOT-323, AN3: SOT-523</p> <p>(3) G: Halogen Free and Lead Free</p>
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### ■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	$V_{CBO}$	-50	V
Collector-Emitter Voltage	$V_{CEO}$	-50	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-100	mA
Collector Power Dissipation	$P_C$	200	mW
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55~+150	$^\circ\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

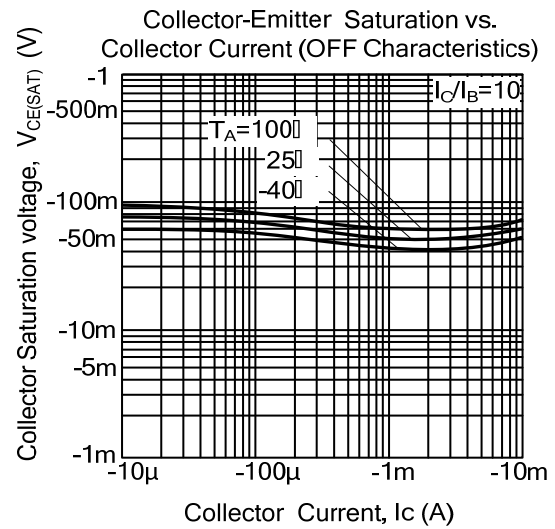
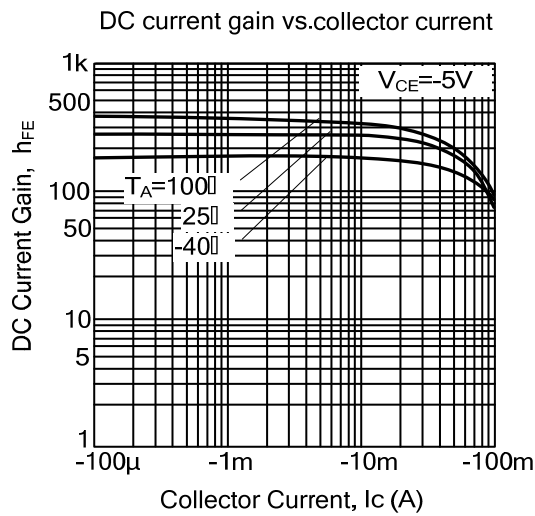
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	$BV_{CBO}$	$I_C = -50\mu\text{A}$	-50			V
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	$I_C = -1\text{mA}$	-50			V
Emitter-Base Breakdown Voltage	$BV_{EBO}$	$I_E = -50\mu\text{A}$	-5			V
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = -50\text{V}$			-0.5	$\mu\text{A}$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = -4\text{V}$			-0.5	$\mu\text{A}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = -5\text{mA}, I_B = -0.5\text{mA}$			-0.3	V
DC Current Transfer Ratio	$h_{FE}$	$V_{CE} = -5\text{V}, I_C = -1\text{mA}$	100	250	600	
Transition Frequency (Note)	$f_T$	$V_{CE} = -10\text{V}, I_E = 5\text{mA}, f = 100\text{MHz}$		250		MHz
Input Resistance	R1		32.9	47	61.1	k $\Omega$

Note: Transition frequency of the device

### ■ TYPICAL CHARACTERISTICS



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.